

AMENDMENTS TO THE CLAIMS:

1. (Previously Presented) A stent comprising a compound including Ti, N, C, or including Ti, N, O, or both, implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent.
2. (Previously Presented) The stent of Claim 21, wherein x is 1 and y is 1 or 2.
3. (Previously Presented) The stent of Claim 21, wherein the depth of the implanted TiN_xO_y compound is not greater than about 2000 Å from the surface of the stent.
4. (Previously Presented) The stent of Claim 21, additionally comprising a layer of TiN_xO_y compound deposited on the region of the surface of the stent where the TiN_xO_y compound is implanted.
5. (Original) The stent of Claim 4, wherein x is 1 and y is 1 or 2.
6. (Original) The stent of Claim 4, wherein the layer of TiN_xO_y compound is not more than about 48,000 Å in thickness.
7. (Original) The stent of Claim 1, wherein the stent is made from stainless steel.
8. (Original) The stent of Claim 1, wherein the surface is the tissue-contacting surface of the stent.
9. (Previously Presented) A stent comprising a layer of TiN_xO_y or TiN_xC_y on a surface of the stent and a subsurface compound including Ti, N, or TiN disposed beneath the layer of TiN_xO_y or TiN_xC_y , wherein the subsurface compound is intermixed with a surface material of the stent.

10. (Previously Presented) The stent of Claim 9, wherein a region of the layer of TiN_xO_y or TiN_xC_y is implanted at a depth within a surface of the stent.
11. (Canceled).
12. (Canceled).
13. (Previously Presented) A method of modifying a surface of a stent, comprising implanting a compound including Ti, N, C, or including Ti, N, O, or both, on a molecular or atomic level at a depth within a surface of the stent.
14. (Previously Presented) The method of Claim 22 wherein x is 1 and y is 1 or 2.
15. (Previously Presented) The method of Claim 22 additionally comprising forming a layer of a TiN_xO_y compound on the surface of the stent where the TiN_xO_y compound is implanted.
16. (Original) The method of Claim 15, wherein x is 1 and y is 1 or 2.
17. (Original) The method of Claim 13, wherein the stent is made from stainless steel.
18. (Previously Presented) The method of Claim 13, wherein prior to the act of implanting the compound including Ti, N, C, or including Ti, N, O, or both, within the surface of the stent, the method comprises implanting Ti, N or TiN within the surface of the stent.
19. (Previously Presented) A method of modifying a stent surface, comprising implanting Ti, N, or TiN into the surface of the stent on a molecular or atomic level

and forming a layer of a TiN_xO_y or or TiN_xC_y compound over at least some of the areas where Ti, N, or TiN has been implanted.

20. (Canceled).
21. (Previously Presented) A stent comprising a TiN_xO_y compound implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent.
22. (Previously Presented) The method of Claim 13, comprising implanting a TiN_xO_y compound at a depth within a surface of the stent.
23. (Previously Presented) A stent comprising a compound including Ti, N, C, or including Ti, N, O, or both, implanted by plasma reaction on a molecular or atomic level at a depth within at least a region of a surface of the stent.
24. (Previously Presented) The stent of Claim 23 wherein the stent is made from stainless steel.
25. (Previously Presented) The stent of Claim 23 wherein the surface is the tissue-contacting surface of the stent.
26. (Previously Presented) The A stent comprising a layer of TiN_xO_y or TiN_xC_y exposed on the surface of the stent, the stent having a surface material different than TiN_xO_y or TiN_xC_y and a compound including Ti, N, or TiN, disposed beneath the layer of TiN_xO_y or TiN_xC_y such that the compound is blended with the surface material of the stent.
27. (Previously Presented) The stent of Claim 26 wherein a region of the layer of

TiN_xO_y or TiN_xC_y is implanted at a depth within a surface of the stent.

28. (Previously Presented) A stent comprising a TiN_xO_y compound implanted by plasma reaction on a molecular or atomic level at a depth within at least a region of a surface of the stent.
29. (Previously Presented) The stent of Claim 28 wherein x is 1 and y is 1 or 2.
30. (Previously Presented) The stent of Claim 28 wherein the depth of the implanted TiN_xO_y compound is not greater than about 2000 Å from the surface of the stent.
31. (Previously Presented) The stent of Claim 28 additionally comprising a layer of TiN_xO_y compound deposited on the region of the surface of the stent where the TiN_xO_y compound is implanted.
32. (Previously Presented) The stent of Claim 31 wherein x is 1 and y is 1 or 2.
33. (Previously Presented) The stent of Claim 31 wherein the layer of TiN_xO_y compound is not more than about 48,000 Å in thickness.
34. (Previously Presented) A stent comprising a TiN_xC_y compound implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent.
35. (Previously Presented) A method of modifying a surface of a stent, comprising implanting by plasma reaction on a molecular or atomic level a compound including Ti, N, C, or including Ti, N, O, or both, at a depth within a surface of the stent.

36. (Previously Presented) The method of Claim 35 additionally comprising forming a layer of a TiN_xO_y compound on the surface of the stent where the TiN_xO_y compound is implanted.
37. (Previously Presented) The method of Claim 35 comprising implanting by plasma reaction a TiN_xO_y compound at a depth within a surface of the stent.
38. (Previously Presented) The method of Claim 36 wherein x is 1 and y is 1 or 2.
39. (Previously Presented) The method of Claim 37 wherein x is 1 and y is 1 or 2.
40. (Previously Presented) The method of Claim 35 wherein the stent is made from stainless steel.
41. (Previously Presented) The method of Claim 35 wherein prior to the act of implanting the compound including Ti, N, C, or including Ti, N, O, or both, within the surface of the stent, the method comprises implanting Ti, N, or TiN within the surface of the stent.
42. (Previously Presented) The stent of Claim 34, additionally comprising a layer of a TiN_xC_y compound on the region of the surface of the stent wherein the TiN_xC_y compound is implanted.
43. (Previously Presented) A method of modifying a stent surface, comprising implanting by plasma reaction on a molecular or atomic level Ti, N, or TiN into the surface of the stent and forming a layer of a TiN_xO_y compound over the areas where Ti, N, or TiN has been implanted.
44. (Previously Presented) A method of modifying a surface of a stent, comprising

implanting a TiN_xC_y compound on a molecular or atomic level at a depth within a surface of the stent or depositing the compound on the surface of the stent.

45. (Previously Presented) The stent of Claim 1, additionally comprising a layer of TiN_xO_y or TiN_xC_y exposed on a surface of the stent.